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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	2566
Number of Logic Elements/Cells	25660
Total RAM Bits	1944576
Number of I/O	473
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-BGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s25b672c7n

Chapter	Date/Version	Changes Made
2	July 2003, v2.0	<ul style="list-style-type: none"> Added reference on page 2-73 to Figures 2-50 and 2-51 for RCLK connections. Updated ranges for EPLL post-scale and pre-scale dividers on page 2-85. Updated PLL Reconfiguration frequency from 25 to 22 MHz on page 2-87. New requirement to assert are set signal each PLL when it has to re-acquire lock on either a new clock after loss of lock (page 2-96). Updated max input frequency for CLK [1, 3, 8, 10] from 462 to 500, Table 2-24. Renamed impedance matching to series termination throughout. Updated naming convention for DQS pins on page 2-112 to match pin tables. Added DDR SDRAM Performance Specification on page 2-117. Added external reference resistor values for terminator technology (page 2-136). Added Terminator Technology Specification on pages 2-137 and 2-138. Updated Tables 2-45 to 2-49 to reflect PLL cross-bank support for high speed differential channels at full speed. Wire bond package performance specification for “high” speed channels was increased to 624 Mbps from 462 Mbps throughout chapter.
3	July 2005, v1.3	<ul style="list-style-type: none"> Updated “Operating Modes” section. Updated “Temperature Sensing Diode” section. Updated “IEEE Std. 1149.1 (JTAG) Boundary-Scan Support” section. Updated “Configuration” section.
	January 2005, v1.2	<ul style="list-style-type: none"> Updated limits for JTAG chain of devices.
	September 2004, v1.1	<ul style="list-style-type: none"> Added new section, “Stratix Automated Single Event Upset (SEU) Detection” on page 3–12. Updated description of “Custom-Built Circuitry” on page 3–13.
	April 2003, v1.0	<ul style="list-style-type: none"> No new changes in <i>Stratix Device Handbook</i> v2.0.
4	January 2006, v3.4	<ul style="list-style-type: none"> Added Table 4–135.
	July 2005, v3.3	<ul style="list-style-type: none"> Updated Tables 4–6 and 4–30. Updated Tables 4–103 through 4–108. Updated Tables 4–114 through 4–124. Updated Table 4–129. Added Table 4–130.

Table 1–5. Stratix FineLine BGA Package Sizes

Dimension	484 Pin	672 Pin	780 Pin	1,020 Pin	1,508 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm ²)	529	729	841	1,089	1,600
Length × width (mm × mm)	23 × 23	27 × 27	29 × 29	33 × 33	40 × 40

Stratix devices are available in up to four speed grades, -5, -6, -7, and -8, with -5 being the fastest. [Table 1–6](#) shows Stratix device speed-grade offerings.

Table 1–6. Stratix Device Speed Grades

Device	672-Pin BGA	956-Pin BGA	484-Pin FineLine BGA	672-Pin FineLine BGA	780-Pin FineLine BGA	1,020-Pin FineLine BGA	1,508-Pin FineLine BGA
EP1S10	-6, -7		-5, -6, -7	-6, -7	-5, -6, -7		
EP1S20	-6, -7		-5, -6, -7	-6, -7	-5, -6, -7		
EP1S25	-6, -7			-6, -7, -8	-5, -6, -7	-5, -6, -7	
EP1S30		-5, -6, -7			-5, -6, -7, -8	-5, -6, -7	
EP1S40		-5, -6, -7			-5, -6, -7, -8	-5, -6, -7	-5, -6, -7
EP1S60		-6, -7				-5, -6, -7	-6, -7
EP1S80		-6, -7				-5, -6, -7	-5, -6, -7

Functional Description

Stratix® devices contain a two-dimensional row- and column-based architecture to implement custom logic. A series of column and row interconnects of varying length and speed provide signal interconnects between logic array blocks (LABs), memory block structures, and DSP blocks.

The logic array consists of LABs, with 10 logic elements (LEs) in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device.

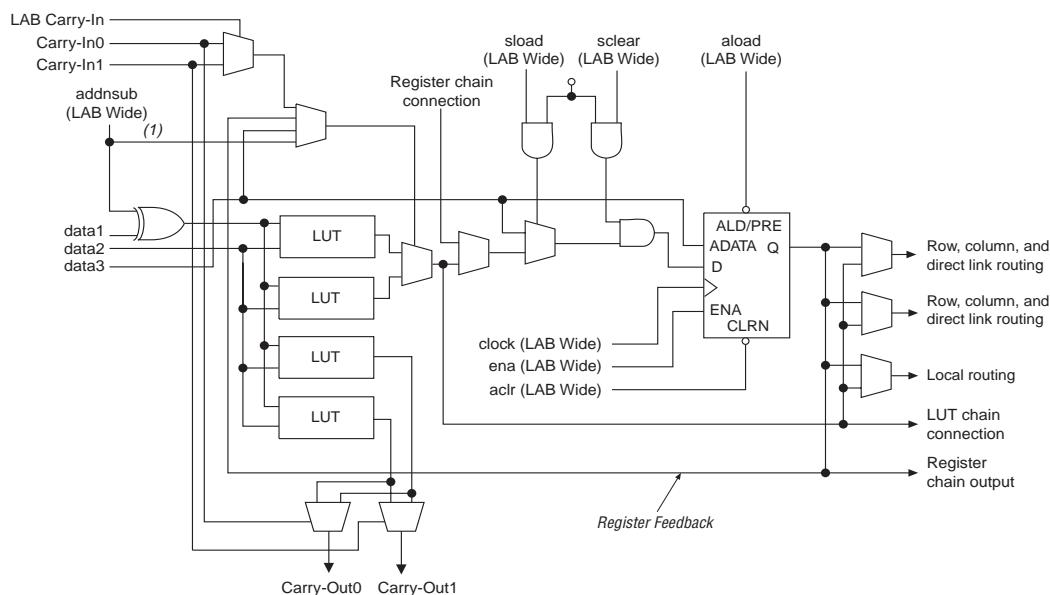
M512 RAM blocks are simple dual-port memory blocks with 512 bits plus parity (576 bits). These blocks provide dedicated simple dual-port or single-port memory up to 18-bits wide at up to 318 MHz. M512 blocks are grouped into columns across the device in between certain LABs.

M4K RAM blocks are true dual-port memory blocks with 4K bits plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 291 MHz. These blocks are grouped into columns across the device in between certain LABs.

M-RAM blocks are true dual-port memory blocks with 512K bits plus parity (589,824 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 144-bits wide at up to 269 MHz. Several M-RAM blocks are located individually or in pairs within the device's logic array.

Digital signal processing (DSP) blocks can implement up to either eight full-precision 9×9 -bit multipliers, four full-precision 18×18 -bit multipliers, or one full-precision 36×36 -bit multiplier with add or subtract features. These blocks also contain 18-bit input shift registers for digital signal processing applications, including FIR and infinite impulse response (IIR) filters. DSP blocks are grouped into two columns in each device.

Each Stratix device I/O pin is fed by an I/O element (IOE) located at the end of LAB rows and columns around the periphery of the device. I/O pins support numerous single-ended and differential I/O standards. Each IOE contains a bidirectional I/O buffer and six registers for registering input, output, and output-enable signals. When used with

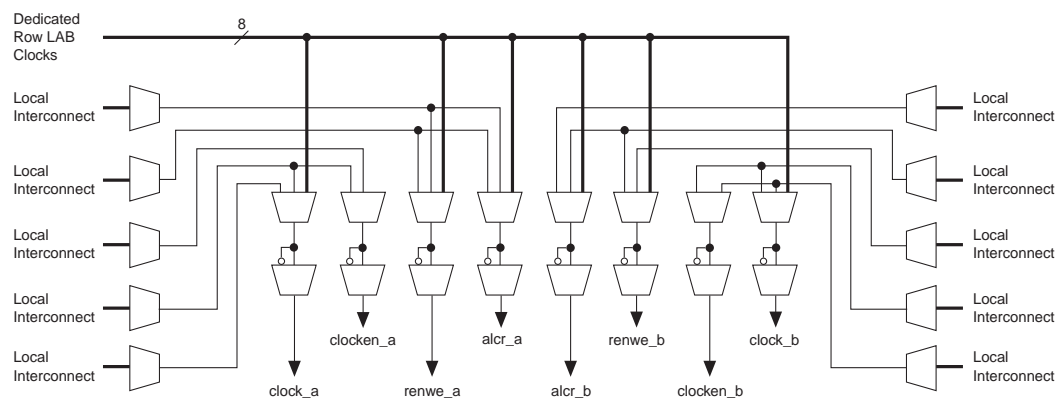
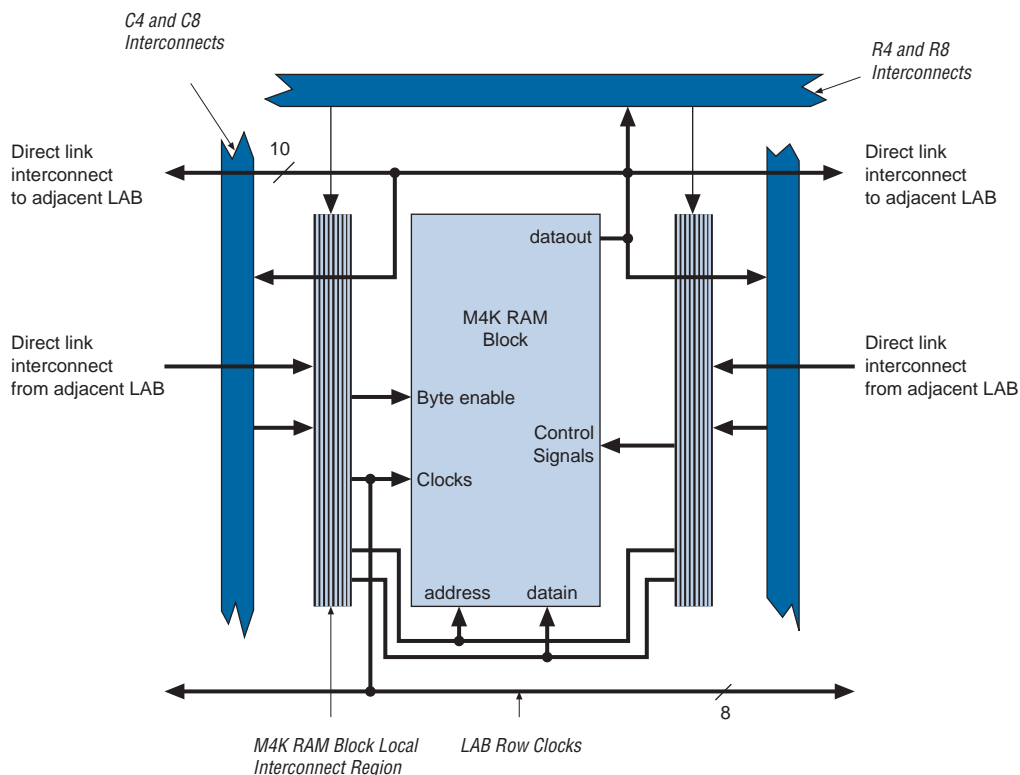
Figure 2–7. LE in Dynamic Arithmetic Mode**Note to Figure 2–7:**

(1) The addnsb signal is tied to the carry input for the first LE of a carry chain only.

Carry-Select Chain

The carry-select chain provides a very fast carry-select function between LEs in arithmetic mode. The carry-select chain uses the redundant carry calculation to increase the speed of carry functions. The LE is configured to calculate outputs for a possible carry-in of 1 and carry-in of 0 in parallel. The carry-in0 and carry-in1 signals from a lower-order bit feed forward into the higher-order bit via the parallel carry chain and feed into both the LUT and the next portion of the carry chain. Carry-select chains can begin in any LE within an LAB.

The speed advantage of the carry-select chain is in the parallel pre-computation of carry chains. Since the LAB carry-in selects the precomputed carry chain, not every LE is in the critical path. Only the propagation delay between LAB carry-in generation (LE 5 and LE 10) are now part of the critical path. This feature allows the Stratix architecture to implement high-speed counters, adders, multipliers, parity functions, and comparators of arbitrary width.

Figure 2–17. M4K RAM Block Control Signals**Figure 2–18. M4K RAM Block LAB Row Interface**

clock signals are routed from LAB row clocks and are generated from specific LAB rows at the DSP block interface. The LAB row source for control signals, data inputs, and outputs is shown in [Table 2–17](#).

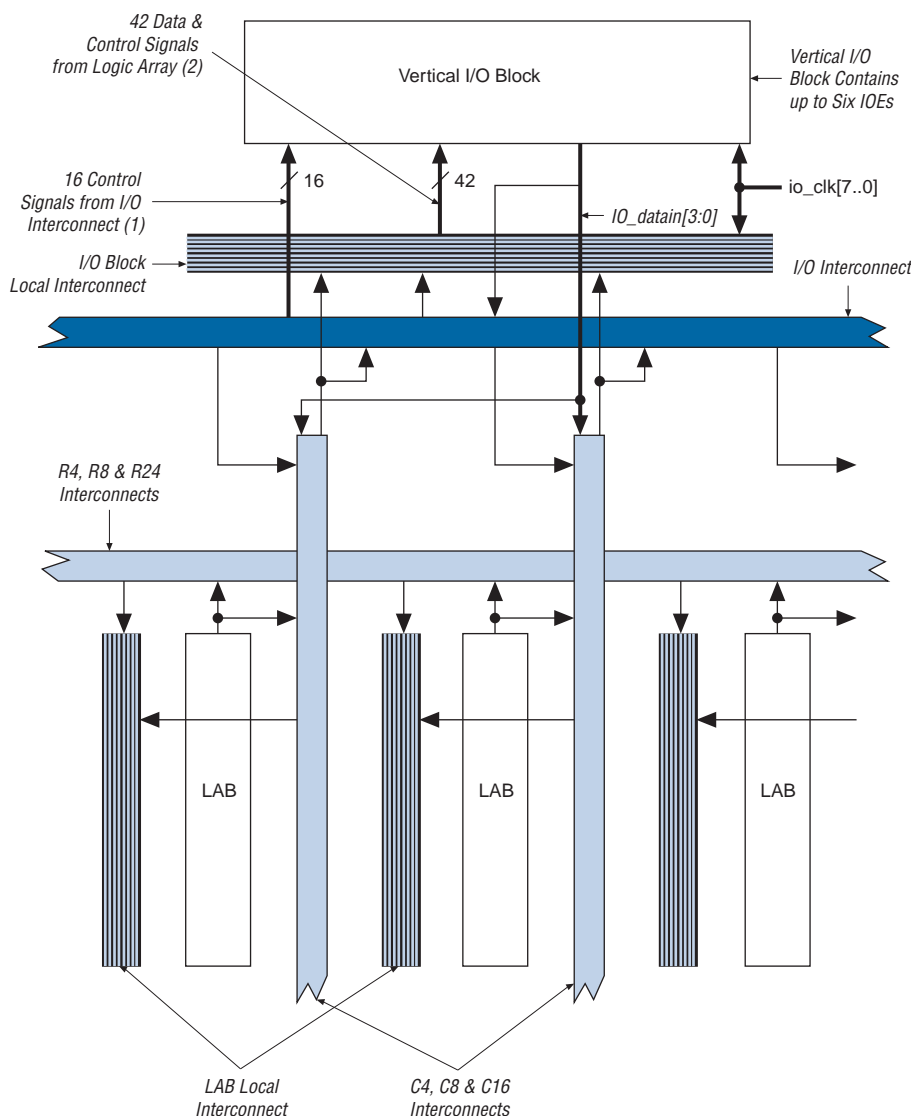
Table 2–17. DSP Block Signal Sources & Destinations			
LAB Row at Interface	Control Signals Generated	Data Inputs	Data Outputs
1	signa	A1 [17..0]	OA [17..0]
2	aclr0 accum_sload0	B1 [17..0]	OB [17..0]
3	addnsb1 clock0 ena0	A2 [17..0]	OC [17..0]
4	aclr1 clock1 ena1	B2 [17..0]	OD [17..0]
5	aclr2 clock2 ena2	A3 [17..0]	OE [17..0]
6	sign_b clock3 ena3	B3 [17..0]	OF [17..0]
7	clear3 accum_sload1	A4 [17..0]	OG [17..0]
8	addnsb3	B4 [17..0]	OH [17..0]

PLLs & Clock Networks

Stratix devices provide a hierarchical clock structure and multiple PLLs with advanced features. The large number of clocking resources in combination with the clock synthesis precision provided by enhanced and fast PLLs provides a complete clock management solution.

Global & Hierarchical Clocking

Stratix devices provide 16 dedicated global clock networks, 16 regional clock networks (four per device quadrant), and 8 dedicated fast regional clock networks (for EP1S10, EP1S20, and EP1S25 devices), and 16 dedicated fast regional clock networks (for EP1S30 EP1S40, and EP1S60, and EP1S80 devices). These clocks are organized into a hierarchical clock structure that allows for up to 22 clocks per device region with low skew and delay. This hierarchical clocking scheme provides up to 48 unique clock domains within Stratix devices.

Figure 2–61. Column I/O Block Connection to the Interconnect**Notes to Figure 2–61:**

- (1) The 16 control signals are composed of four output enables `io_boe[3..0]`, four clock enables `io_bce[3..0]`, four clocks `io_bclk[3..0]`, and four clear signals `io_bclr[3..0]`.
- (2) The 42 data and control signals consist of 12 data out lines; six lines each for DDR applications `io_dataouta[5..0]` and `io_dataoutb[5..0]`, six output enables `io_coe[5..0]`, six input clock enables `io_cce_in[5..0]`, six output clock enables `io_cce_out[5..0]`, six clocks `io_cclk[5..0]`, and six clear signals `io_cclr[5..0]`.

Figure 3–5. External Temperature-Sensing Diode

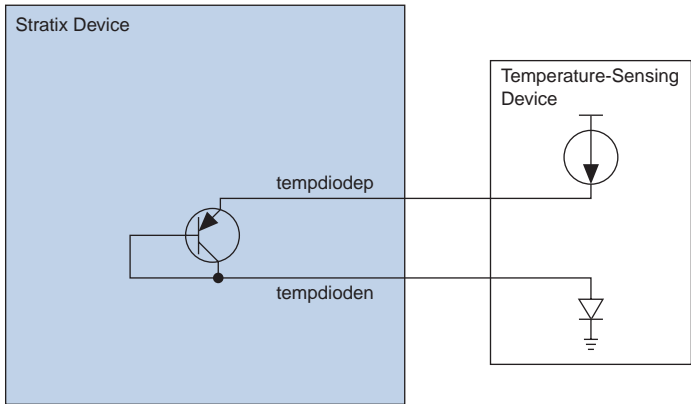


Table 3–6 shows the specifications for bias voltage and current of the Stratix temperature sensing diode.

Table 3–6. Temperature-Sensing Diode Electrical Characteristics				
Parameter	Minimum	Typical	Maximum	Unit
$I_{\text{BIAS high}}$	80	100	120	μA
$I_{\text{BIAS low}}$	8	10	12	μA
$V_{\text{BP}} - V_{\text{BN}}$	0.3		0.9	V
V_{BN}		0.7		V
Series resistance			3	W

Table 4–7. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V _{CCIO}	Output supply voltage		1.65	1.95	V
V _{IH}	High-level input voltage		0.65 × V _{CCIO}	2.25	V
V _{IL}	Low-level input voltage		–0.3	0.35 × V _{CCIO}	V
V _{OH}	High-level output voltage	I _{OH} = –2 to –8 mA (10)	V _{CCIO} – 0.45		V
V _{OL}	Low-level output voltage	I _{OL} = 2 to 8 mA (10)		0.45	V

Table 4–8. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V _{CCIO}	Output supply voltage		1.4	1.6	V
V _{IH}	High-level input voltage		0.65 × V _{CCIO}	V _{CCIO} + 0.3	V
V _{IL}	Low-level input voltage		–0.3	0.35 × V _{CCIO}	V
V _{OH}	High-level output voltage	I _{OH} = –2 mA (10)	0.75 × V _{CCIO}		V
V _{OL}	Low-level output voltage	I _{OL} = 2 mA (10)		0.25 × V _{CCIO}	V

Notes to Tables 4–1 through 4–8:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Conditions beyond those listed in Table 4–1 may cause permanent damage to a device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse affects on the device.
- (3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns, or overshoot to the voltage shown in Table 4–9, based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.
- (4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
- (5) V_{CCIO} maximum and minimum conditions for LVPECL, LVDS, and 3.3-V PCML are shown in parentheses.
- (6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (7) Typical values are for T_A = 25°C, V_{CCINT} = 1.5 V, and V_{CCIO} = 1.5 V, 1.8 V, 2.5 V, and 3.3 V.
- (8) This value is specified for normal device operation. The value may vary during power-up. This applies for all V_{CCIO} settings (3.3, 2.5, 1.8, and 1.5 V).
- (9) Pin pull-up resistance values will lower if an external source drives the pin higher than V_{CCIO}.
- (10) Drive strength is programmable according to the values shown in the *Stratix Architecture* chapter of the *Stratix Device Handbook, Volume 1*.

Table 4–9. Overshoot Input Voltage with Respect to Duty Cycle (Part 1 of 2)

V _{in} (V)	Maximum Duty Cycle (%)
4.0	100
4.1	90
4.2	50

Performance

Table 4–36 shows Stratix performance for some common designs. All performance values were obtained with Quartus II software compilation of LPM, or MegaCore® functions for the FIR and FFT designs.

Table 4–36. Stratix Performance (Part 1 of 2) Notes (1), (2)

Applications		Resources Used			Performance				
		LEs	TriMatrix Memory Blocks	DSP Blocks	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Units
LE	16-to-1 multiplexer (1)	22	0	0	407.83	324.56	288.68	228.67	MHz
	32-to-1 multiplexer (3)	46	0	0	318.26	255.29	242.89	185.18	MHz
	16-bit counter	16	0	0	422.11	422.11	390.01	348.67	MHz
	64-bit counter	64	0	0	321.85	290.52	261.23	220.5	MHz
TriMatrix memory M512 block	Simple dual-port RAM 32 × 18 bit	0	1	0	317.76	277.62	241.48	205.21	MHz
	FIFO 32 × 18 bit	30	1	0	319.18	278.86	242.54	206.14	MHz
TriMatrix memory M4K block	Simple dual-port RAM 128 × 36 bit	0	1	0	290.86	255.55	222.27	188.89	MHz
	True dual-port RAM 128 × 18 bit	0	1	0	290.86	255.55	222.27	188.89	MHz
	FIFO 128 × 36 bit	34	1	0	290.86	255.55	222.27	188.89	MHz
TriMatrix memory M-RAM block	Single port RAM 4K × 144 bit	1	1	0	255.95	223.06	194.06	164.93	MHz
	Simple dual-port RAM 4K × 144 bit	0	1	0	255.95	233.06	194.06	164.93	MHz
	True dual-port RAM 4K × 144 bit	0	1	0	255.95	233.06	194.06	164.93	MHz
	Single port RAM 8K × 72 bit	0	1	0	278.94	243.19	211.59	179.82	MHz
	Simple dual-port RAM 8K × 72 bit	0	1	0	255.95	223.06	194.06	164.93	MHz
	True dual-port RAM 8K × 72 bit	0	1	0	255.95	223.06	194.06	164.93	MHz
	Single port RAM 16K × 36 bit	0	1	0	280.66	254.32	221.28	188.00	MHz
	Simple dual-port RAM 16K × 36 bit	0	1	0	269.83	237.69	206.82	175.74	MHz

Table 4–42. M-RAM Block Internal Timing Microparameter Descriptions (Part 2 of 2)

Symbol	Parameter
$t_{\text{MRAMDATA BH}}$	B port hold time after clock
$t_{\text{MRAMADDR BSU}}$	B port address setup time before clock
$t_{\text{MRAMADDR BH}}$	B port address hold time after clock
$t_{\text{MRAMDATA CO1}}$	Clock-to-output delay when using output registers
$t_{\text{MRAMDATA CO2}}$	Clock-to-output delay without output registers
$t_{\text{MRAMCLK HL}}$	Register minimum clock high or low time. This is a limit on the min time for the clock on the registers in these blocks. The actual performance is dependent upon the internal point-to-point delays in the blocks and may give slower performance as shown in Table 4–36 on page 4–20 and as reported by the timing analyzer in the Quartus II software.
t_{MRAMCLR}	Minimum clear pulse width.

Table 4–59. EP1S10 External I/O Timing on Row Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.161		2.336		2.685		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.434	4.889	2.434	5.226	2.434	5.643	NA	NA	ns
t_{XZ}	2.461	4.493	2.461	5.282	2.461	5.711	NA	NA	ns
t_{ZX}	2.461	4.493	2.461	5.282	2.461	5.711	NA	NA	ns
t_{INSUPLL}	1.057		1.172		1.315		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.327	2.773	1.327	2.848	1.327	2.940	NA	NA	ns
t_{XZPLL}	1.354	2.827	1.354	2.904	1.354	3.008	NA	NA	ns
t_{ZXPLL}	1.354	2.827	1.354	2.904	1.354	3.008	NA	NA	ns

Table 4–60. EP1S10 External I/O Timing on Row Pins Using Global Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.787		1.944		2.232		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.647	5.263	2.647	5.618	2.647	6.069	NA	NA	ns
t_{XZ}	2.674	5.317	2.674	5.674	2.674	6.164	NA	NA	ns
t_{ZX}	2.674	5.317	2.674	5.674	2.674	6.164	NA	NA	ns
t_{INSUPLL}	1.371		1.1472		1.654		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.144	2.459	1.144	2.548	1.144	2.601	NA	NA	ns
t_{XZPLL}	1.171	2.513	1.171	2.604	1.171	2.669	NA	NA	ns
t_{ZXPLL}	1.171	2.513	1.171	2.604	1.171	2.669	NA	NA	ns

Note to Tables 4–55 to 4–60:

(1) Only EP1S25, EP1S30, and EP1S40 have speed grade of -8.

Table 4–65. EP1S20 External I/O Timing on Row Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.815		1.967		2.258		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.633	5.235	2.663	5.595	2.663	6.070	NA	NA	ns
t_{XZ}	2.660	5.289	2.660	5.651	2.660	6.138	NA	NA	ns
t_{ZX}	2.660	5.289	2.660	5.651	2.660	6.138	NA	NA	ns
t_{INSUPLL}	1.060		1.112		1.277		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.325	2.770	1.325	2.908	1.325	2.978	NA	NA	ns
t_{XZPLL}	1.352	2.824	1.352	2.964	1.352	3.046	NA	NA	ns
t_{ZXPLL}	1.352	2.824	1.352	2.964	1.352	3.046	NA	NA	ns

Table 4–66. EP1S20 External I/O Timing on Row Pins Using Global Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.742		1.887		2.170		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.674	5.308	2.674	5.675	2.674	6.158	NA	NA	ns
t_{XZ}	2.701	5.362	2.701	5.731	2.701	6.226	NA	NA	ns
t_{ZX}	2.701	5.362	2.701	5.731	2.701	6.226	NA	NA	ns
t_{INSUPLL}	1.353		1.418		1.613		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.158	2.447	1.158	2.602	1.158	2.642	NA	NA	ns
t_{XZPLL}	1.185	2.531	1.158	2.602	1.185	2.710	NA	NA	ns
t_{ZXPLL}	1.185	2.531	1.158	2.602	1.185	2.710	NA	NA	ns

Note to Tables 4–61 to 4–66:

(1) Only EP1S25, EP1S30, and EP1S40 have a speed grade of -8.

Table 4–87. EP1S60 External I/O Timing on Column Pins Using Global Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.000		2.152		2.441		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	3.051	5.900	3.051	6.340	3.051	6.977	NA	NA	ns
t_{XZ}	2.991	5.774	2.991	6.208	2.991	6.853	NA	NA	ns
t_{ZX}	2.991	5.774	2.991	6.208	2.991	6.853	NA	NA	ns
t_{INSUPLL}	1.315		1.362		1.543		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.029	2.196	1.029	2.303	1.029	2.323	NA	NA	ns
t_{XZPLL}	0.969	2.070	0.969	2.171	0.969	2.199	NA	NA	ns
t_{ZXPLL}	0.969	2.070	0.969	2.171	0.969	2.199	NA	NA	ns

Table 4–88. EP1S60 External I/O Timing on Row Pins Using Fast Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	3.144		3.393		3.867		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.643	5.275	2.643	5.654	2.643	6.140	NA	NA	ns
t_{XZ}	2.670	5.329	2.670	5.710	2.670	6.208	NA	NA	ns
t_{ZX}	2.670	5.329	2.670	5.710	2.670	6.208	NA	NA	ns

Table 4–97. Output Pin Timing Skew Definitions (Part 2 of 2)

Symbol	Definition
t_{LR_HIO}	Across all HIO banks (1, 2, 5, 6); across four similar type I/O banks
t_{TB_VIO}	Across all VIO banks (3, 4, 7, 8); across four similar type I/O banks
$t_{OVERALL}$	Output timing skew for all I/O pins on the device.

Notes to Table 4–97:

- (1) See Figure 4–5 on page 4–57.
- (2) See Figure 4–6 on page 4–58.

Table 4–98 shows the I/O skews when using the same global or regional clock to feed IOE registers in I/O banks around each device. These values can be used for calculating the timing budget on the output (write) side of a memory interface. These values already factor in the package skew.

Table 4–98. Output Skew for Stratix by Device Density

Symbol	Skew (ps) (1)		
	EP1S10 to EP1S30	EP1S40	EP1S60 & EP1S80
t_{SB_HIO}	90	290	500
t_{SB_VIO}	160	290	500
t_{SS_HIO}	90	460	600
t_{SS_VIO}	180	520	630
t_{LR_HIO}	150	490	600
t_{TB_VIO}	190	580	670
$t_{OVERALL}$	430	630	880

Note to Table 4–98:

- (1) The skew numbers in Table 4–98 account for worst case package skews.

Table 4–101. Reporting Methodology For Maximum Timing For Single-Ended Output Pins (Part 2 of 2)
Notes (1), (2), (3)

I/O Standard	Loading and Termination							Measurement Point
	R_{UP} Ω	R_{DN} Ω	R_S Ω	R_T Ω	V_{CCIO} (V)	V_{TT} (V)	C_L (pF)	V_{MEAS}
3.3-V SSTL-3 Class I	–	–	25	50	2.950	1.250	30	1.250
2.5-V SSTL-2 Class II	–	–	25	25	2.370	1.110	30	1.110
2.5-V SSTL-2 Class I	–	–	25	50	2.370	1.110	30	1.110
1.8-V SSTL-18 Class II	–	–	25	25	1.650	0.760	30	0.760
1.8-V SSTL-18 Class I	–	–	25	50	1.650	0.760	30	0.760
1.5-V HSTL Class II	–	–	0	25	1.400	0.700	20	0.680
1.5-V HSTL Class I	–	–	0	50	1.400	0.700	20	0.680
1.8-V HSTL Class II	–	–	0	25	1.650	0.700	20	0.880
1.8-V HSTL Class I	–	–	0	50	1.650	0.700	20	0.880
3.3-V PCI (4)	–/25	25/–	0	–	2.950	2.950	10	0.841/1.814
3.3-V PCI-X 1.0 (4)	–/25	25/–	0	–	2.950	2.950	10	0.841/1.814
3.3-V Compact PCI (4)	–/25	25/–	0	–	2.950	2.950	10	0.841/1.814
3.3-V AGP 1X (4)	–/25	25/–	0	–	2.950	2.950	10	0.841/1.814
3.3-V CTT	–	–	25	50	2.050	1.350	30	1.350

Notes to Table 4–101:

- (1) Input measurement point at internal node is $0.5 \times V_{CCINT}$.
- (2) Output measuring point for data is V_{MEAS} .
- (3) Input stimulus edge rate is 0 to V_{CCINT} in 0.5 ns (internal signal) from the driver preceding the IO buffer.
- (4) The first value is for output rising edge and the second value is for output falling edge. The hyphen (-) indicates infinite resistance or disconnection.

process and operating conditions. Run the timing analyzer in the Quartus II software at the fast and slow operating conditions to see the phase shift range that is achieved below these frequencies.

Table 4–135. Stratix DLL Low Frequency Limit for Full Phase Shift

Phase Shift	Minimum Frequency for Full Phase Shift	Unit
72°	119	MHz
90°	149	MHz

Figure 5–1. Stratix Device Packaging Ordering Information

